

- Magnetoresisitve sensor technology
- Linear signal output
- Over increased field range
- Very low hysteresis
- High sensititvity
- Substitutes KMZ10C / NXP

#### **DESCRIPTION**

Due to its featured properties - high sensitivity and almost no hysteresis – the **KMZ10CM** sensor is used in a wide range of applications, like magnetic field measurement, revolution counters, proximity detecting, and position measurement.

#### **FEATURES**

- Wheatsone bridge
- Passive output signal
- Linear signal output proportional to magnetic field strength
- 4 lead package for measurement of z direction

#### **APPLICATIONS**

Detection of small magnetic fields, as in:

- · Contactless switch
- · Contactless displacement measurement
- · Current measurement

Polarity detection of small magnetic fields

#### PERFORMANCE SPECS

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
A. Operating Limits 1)							
max. supply voltage	$V_{CC,max}$				10	V	
operating temperature	T <sub>op</sub>		-40		+150	°C	
storage temperature	T <sub>st</sub>		-65		+165	°C	
B. Sensor Specifications (T = 25 °C; H <sub>X</sub> = 3 kA/m)							
supply voltage	V <sub>CC</sub>			5	10	V	
bridge resistance	$R_b$		1000	1400	1800	Ω	
offset voltage	$V_{OFF}/V_{CC}$	H <sub>x</sub> =0	-1.5	0	+1.5	mV/V	
sensitivity	S	note 2	1	1.2	2	(mV/V)/(kA/m)	
hysteresis	$V_{HYST}$	note 3	-	-	100	μV/V	
linearity deviation	FL	note 4	-	-	6.5	%	
C. Sensor Specifications ( $T_{low} = 30  ^{\circ}\text{C}$ ; $T_{high} = 80  ^{\circ}\text{C}$ ; $H_X = 3  \text{kA/m}$ ; $V_{CC} = 5  \text{V}$ )							
TC of sensitivity	TCS	note 5	-	- 0.35	-	%/K	
TC of resistance	TCBR	note 6	-	+ 0.45	-	%/K	
TC of offset	TCV <sub>off</sub>	note 7,8, H <sub>x</sub> =0	-4	0	+4	μV/V/K	

- 1) Stress above one or more of the limiting values may cause permanent damage to the device. Exposure to limiting values for extended periods may affect device reliability.
- 2) The sensitivity is defined as the average slope of characteristic between Hy=0 and 6 kA/m and Hx=3kA/m:

$$S = \frac{V_0(H_y = 6kA/m) - V_0(H_y = 0)}{6*V_{CC}}$$

3) Hysteresis is defined as the difference between offset voltages measured without Hy-field after premagnetization by negative and positive Hy=±6 kA/m field:

$$V_{HYST} = V_0(H_1 \to H_0) - V_0(-H_1 \to H_0); H_0 = 0; H_1 = 6\frac{kA}{m}; H_X = 3\frac{kA}{m}; V_{CC} = 5V$$

4) The linearity error is the deviation of output voltage measured at Hy=3 kA/m from the average of Hy=0 and 6 kA/m-output voltages, expressed as percentage of the output voltage difference measured between 0 and 6 kA/m:

$$FL = \left| \frac{1}{2} - \frac{V_0(H_y = 3kA/m) - V_0(H_y = 0)}{V_0(H_y = 6kA/m) - V_0(H_y = 0)} \right| *100\%$$

5) The temperature coefficient of sensitivity is defined as the percentage change of the sensitivity per K referred to the value at T<sub>1</sub> = -25 °C; T<sub>2</sub>= operating temperature:

$$TCS = \frac{1}{(T_2 - T_1)} * \frac{S(T_2) - S(T_1)}{S(T_1)} * 100\%$$

6) The temperature coefficient of resistance is defined as the percentage change of the resistance per K referred to the value at  $T_1 = -25$  °C;  $T_2 =$  operating temperature:

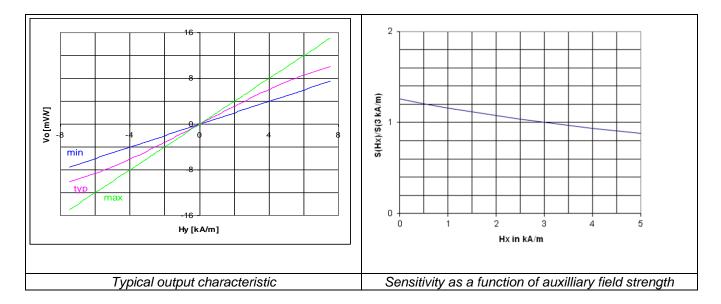
$$TCBR = \frac{1}{(T_2 - T_1)} * \frac{R(T_2) - R(T_1)}{R(T_1)} * 100\%$$

7) Temperature coefficient of offset voltage is defined as the voltage change per K expressed in  $\mu V/V$ :

$$TCV_{off} = \frac{V_{off}(T_2) - V_{off}(T_1)}{(T_2 - T_1)}$$

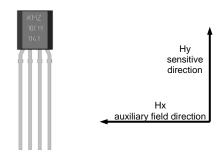
8) Linear behaviour assumed

#### **TYPICAL PERFORMANCE CURVES**



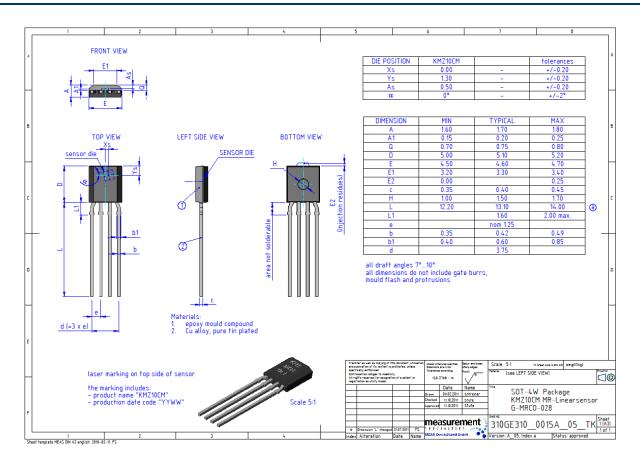
#### **FUNCTION**

#### **TERMINAL CONNECTIONS**



Pin	Symbol	Function
1	+Vo	positive output voltage
2	GND	negative supply voltage
3	-Vo	negative output voltage
4	+Vcc	positive supply voltage

### **BLOCK DIAGRAM**



### **ORDERING CODE**

Product	Description	Part number	
KMZ10CM	KMZ10 CM Linear Field Sensor	G-MRCO-028	

## 联系方式



广东省深圳市南山区创业路怡海广场东座2407 邮编:518000 电话:+86 755 2641 9890 传真:+86 755 2641 9680

电子邮箱:sales@bill-well.com